National Semiconductor

MM74HCA138 3-to-8 Line Decoder

General Description

This decoder utilizes advanced silicon-gate CMOS technology, and is well suited to memory address decoding or data routing applications. The circuit features high noise immunity and low power consumption usually associated with CMOS circuitry, yet has speeds comparable to low power Schottky TTL logic.

The MM74HCA138 has 3 binary select inputs (A, B, and C). If the device is enabled these inputs determine which one of the eight normally high cutputs will go low. Two active low and one active high enables (G1, $\overline{G2A}$ and $\overline{G2B}$) are provided to ease the cascading of decoders.

The decoder's outputs can drive 10 low power Schottky TTL equivalent loads, and are functionally and pin equivalent to the 54LS138/74LS138. All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical propagation delay: 17 ns
- Wide power supply range: 2V-6V
- Low quiescent current: 40 μA maximum
- Low input current: 1 µA maximum Fanout of 10 LS-TTL loads
- Low output noise generation
- QOS specifications V_{OLV}, V_{OLD}
- Identical pinout to HC
- Speed upgrade to HC



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November 1995

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Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.5 to +7.0V
DC Input Voltage (VIN)	-1.5 to V _{CC} $+1.5$ V
DC Output Voltage (V _{OUT})	-0.5 to V _{CC} $+0.5$ V
Clamp Diode Current (I _{IK} , I _{OK})	±20 mA
DC Output Current, per pin (I _{OUT})	±25 mA
DC V _{CC} or GND Current, per pin (I _{CC})	±50 mA
Storage Temperature Range (T _{STG})	-65°C to +150°C
Power Dissipation (PD)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (TL) (Soldering 10 seconds)	260°C

	Min	Max	Units
Supply Voltage (V _{CC})	2	6	V
DC Input or Output Voltage (VIN, VOUT)	0	Vcc	v
Operating Temp. Range (T _A) MM74HCA	- 40	+85	°C
Input Rise or Fall Times			
$(t_r, t_f) V_{CC} = 2.0 V$		1000	ns
$V_{CC} = 4.5V$		500	ns
$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	Vcc	T _A = 25°C		74HCA T _A = -40 to 85°C	Units
				Тур	Gu	aranteed Limits	<u> </u>
VIH	Minimum High Level Input Voltage		2.0V 3.0V 4.5V 6.0V		1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	
V _{IL}	Maximum Low Level Input Voltage		2.0V 3.0V 4.5V 6.0V		0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	v v v
V _{OH} Minimum High Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤20 μA	2.0V 3.0V 4.5V 6.0V	2.0 3.0 4.5 6.0	1.9 2.9 4.4 5.9	1.9 2.9 4.4 5.9	V V V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 4.0 \text{ mA}$ $ I_{OUT} \le 5.2 \text{ mA}$	3.0V 4.5V 6.0V	2.78 4.28 5.78	2.68 4.18 5.68	2.63 4.13 5.63	V V V
V _{OL} Maximum Low Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤20 μA	2.0V 3.0V 4.5V 6.0V	0 0 0 0	0.1 0.1 0.1 0.1	0.1 0.1 0.1 0.1	> > > >	
		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	3.0V 4.5V 6.0V	0.2 0.2 0.2	0.26 0.26 0.26	0.33 0.33 0.33	v v v
I _{IN}	Maximum Input Current	V _{IN} = V _{CC} or GND	6.0V		±0.1	± 1.0	μA
lcc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC} \text{ or GND}$ $I_{OUT} = 0 \ \mu A$	6.0V		4.0	40.0	μΑ
VOLP	Quiet Output Max Dynamic V _{OL}	Figures 1, 2 (Note 5)	5.5V	0.550			v
VOLV	Quiet Output Min Dynamic V _{OL}	Figures 1, 2 (Note 5)	5.5V	-0.750			v

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 55°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C. Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{CH}, and V_{OL}) occur for HCA at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC}=5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

Note 5: n = number of device outputs, n-1 outputs switching, each driven 0V to 5.5V, one output at ground.

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Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t _{PLH}	Maximum Propagation Delay, Binary Select to any Output		12	26	ns
t _{PHL}	Maximum Propagation Delay, Binary Select to any Output		17	26	ns
t₽HL	Maximum Propagation Delay G2A or G2B or G1 to Output		12	25	ns
^t ₽LH	Maximum Propagation Delay G2A or G2B or G1 to Output		10	25	nş

AC Electrical Characteristics $C_L = 50 \text{ pF}$, $t_r = t_f = 6 \text{ ns}$ (unless otherwise specified)

Symbol	Parameter	Conditions	Vcc	T _A =25℃		74HCA T _A =40 to 85°C	Units
				Тур	Gι	uaranteed Limits	
^t РLН	Maximum Propagation		2.0V	75	150	189	ns
	Delay Binary Select to		3.3V	23	45	57	ns
	any Output Low to High		4.5V	15	30	38	ns
			6.0V	13	26	32	ns
ŧрнц	Maximum Propagation		2.0V	100	150	189	ns
	Delay Binary Select to any		3.3V	30	45	57	ns
	Output High to Low		4.5V	20	30	38	ns
			6.0V	17	26	32	ns
ŧрнц	Maximum Propagation		2.0V	75	145	180	ns
	Delay G2A or G2B or		3.3V	23	42	54	ns
	G1 to Output		4.5V	15	29	36	ns
			6.0V	13	25	31	ns
t₽LH	Maximum Propagation		2.0V	60	145	180	ns
	Delay G2A or G2B or		3.3V	18	44	54	ns
	G1 to Output		4.5V	12	29	36	ns
			6.0V	10	25	31	ns
t _{TLH} , t _{THL}	Output Rise and		2.0V	30	75	95	ns
	Fall Time		3.3∨	12	75	95	ns
			4.5V	8	15	19	ns
			6.0V	7	13	16	ns
C _{IN}	Maximum Input Capacitance			3	10	10	pF
C _{PD}	Power Dissipation Capacitance	(Note 5)		75			pF

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